

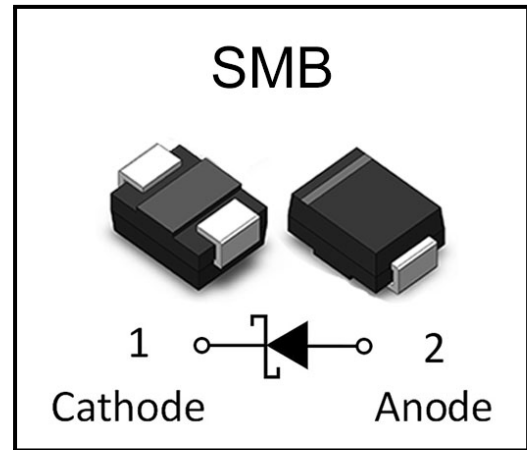
SS1020-SS10200

Schottky Barrier Diode

Features

- Low forward voltage drop
- Guarding protection
- Glass passivated junction
- High current capability
- High efficiency operation
- Extremely low thermal resistance
- Halogen free and RoHS compliant

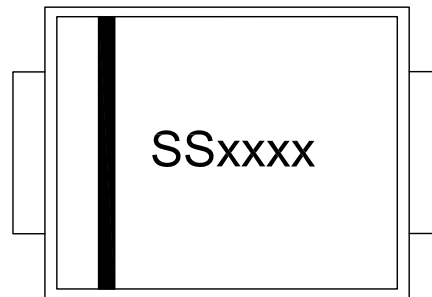
Package



Description

- Case: JEDEC DO-214AA molded plastic
- Terminals: Axial leads. Solderable per MIL-STD-750 Method 2026
- Polarity: Color band denotes cathode
- Mounting Position: Any

Marking



Ordering information

Part Number	SS1020	SS1030	SS1040	SS1050	SS1060	SS1080	SS10100	SS10150	SS10200
Marking	SS1020	SS1030	SS1040	SS1050	SS1060	SS1080	SS10100	SS10150	SS10200
Base qty	3K	3K	3K	3K	3K	3K	3K	3K	3K



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Maximum Ratings and Electrical Characteristics@T_A=25°C unless otherwise noted

Symbol	Parameter	SS 1020	SS 1030	SS 1040	SS 1050	SS 1060	SS 1080	SS 10100	SS 10150	SS 10200	Units
V _{RRM}	Maximum Repetitive Peak Reverse Voltage	20	30	40	50	60	80	100	150	200	V
V _{RWS}	Maximum RMS Voltage	14	21	28	35	42	56	70	105	140	
V _{DC}	Maximum DC Blocking Voltage	20	30	40	50	60	80	100	150	200	
I _{F(AV)}	Maximum average forward Rectified Current	10									A
I _{FSM}	Non-repetitive peak forward surge current 8.3 ms singlehalf sine-wave	150									A
V _F	Maximum instantaneous forward Voltage at I _F =10A	0.55			0.70		0.85		0.95		V
I _R	Maximum DC reverse current T _A =25°C at rated DC blocking voltage T _A =100°C	0.5					0.1				mA
		20					5.0				
T _J	Operating Junction Temperature Range	-55 to +150									°C
T _{STG}	Storage Temperature Range	-55 to +150									
R _{θJA}	Thermal Resistance ⁽¹⁾	65									°C/W
R _{θJL}		8									

Note:(1)Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.6" x 0.6" (16 mm x 16 mm) copper pad areas.



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Typical Performance Characteristics($T_J = 25^\circ\text{C}$, unless otherwise noted)

Figure 1: I_O - T_L Curve

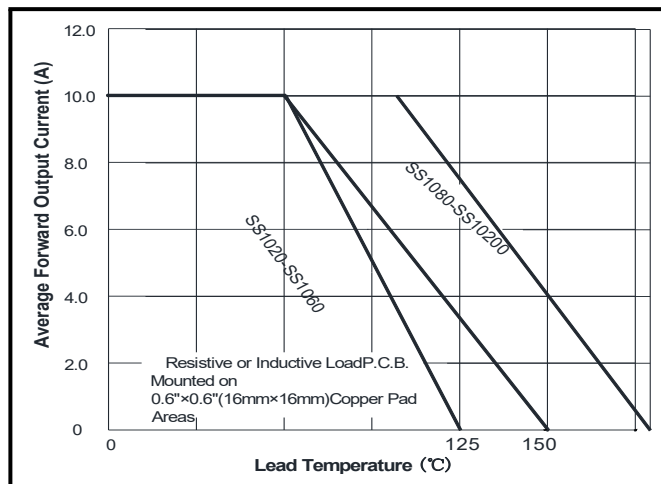


Figure 2: Forward Surge Current Capability

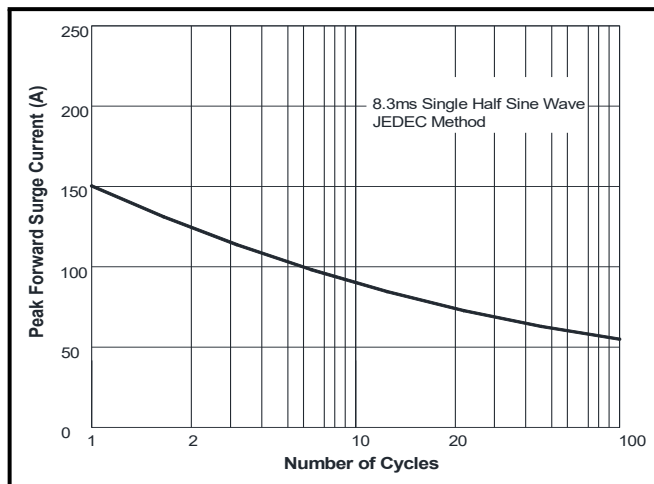


Figure 3: Forward Voltage

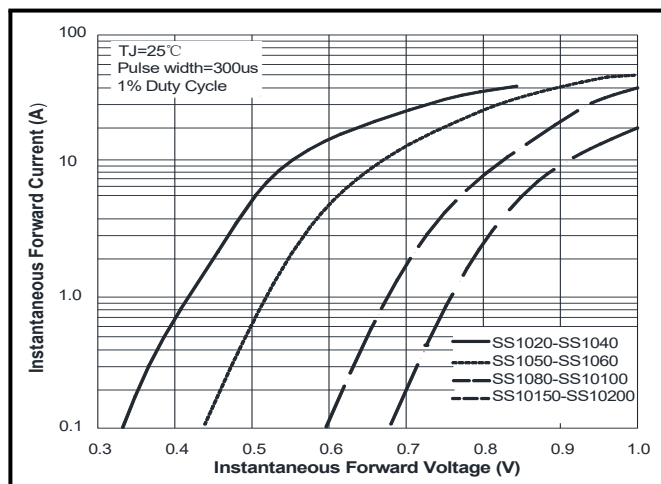
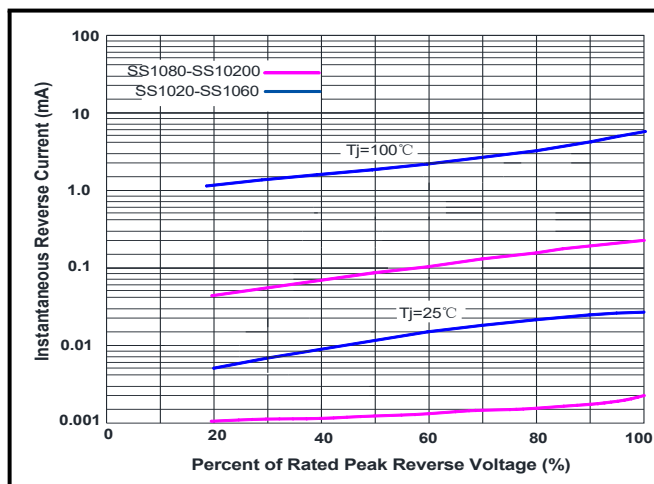


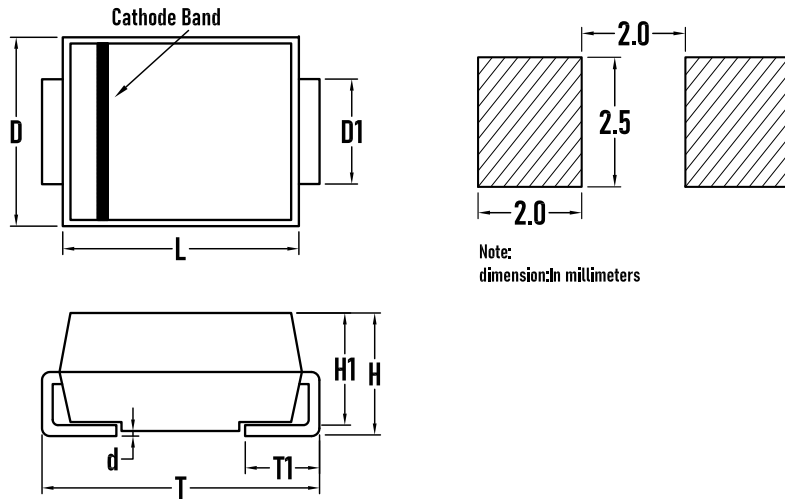
Figure 4: Typical Reverse Characteristics



SS1020-SS10200

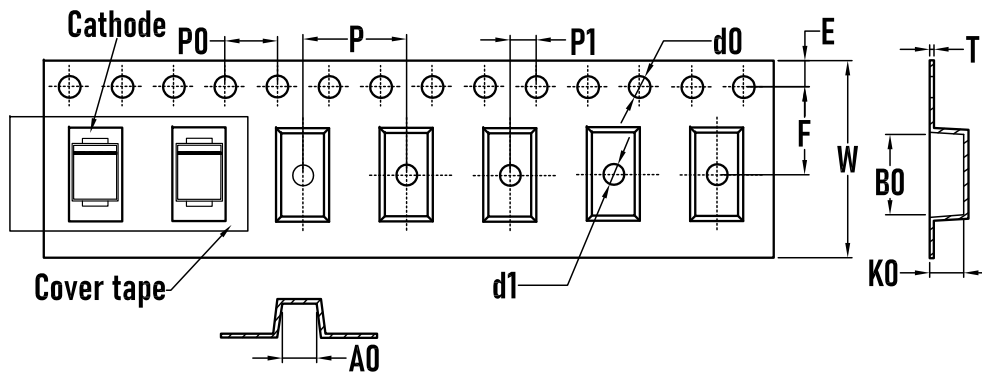
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Outline Drawing - SMB



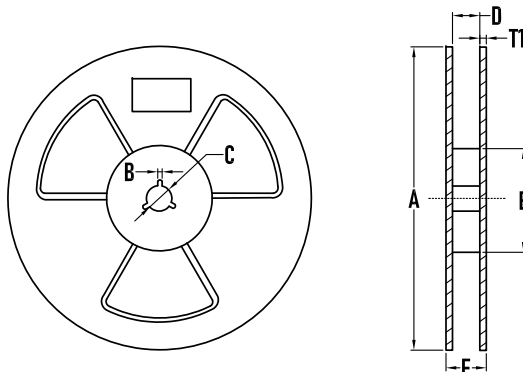
SYMBOL	MILLIMETER		Inches	
	MIN.	MAX.	MIN.	MAX.
D	3.3	3.9	0.130	0.154
D1	1.7	2.3	0.067	0.091
T	5.1	5.7	0.201	0.224
T1	0.8	1.6	0.031	0.063
d	—	0.3	—	0.012
H1	2.0	2.4	0.079	0.094
H	2.1	2.5	0.083	0.098
L	4.0	4.7	0.157	0.185

Packaging Tape - SMB



SYMBOL	MILLIMETER
A0	3.60±0.1
B0	5.45±0.1
d0	1.50±0.1
d1	1.50±0.1
E	1.75±0.1
F	5.50±0.1
K0	2.30±0.1
P	8.00±0.1
P0	4.00±0.1
P1	2.00±0.1
W	12.00±0.1
T	0.22±0.02

Packaging Reel



SYMBOL	MILLIMETER
A	323±2
B	3.0±0.2
C	15.0±0.5
D	13±2
E	73±2
T1	2.2±0.2
Quantity	3000PCS

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Specifications are subject to change without notice.

Please refer to <http://www.born-tw.com> for current information.

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